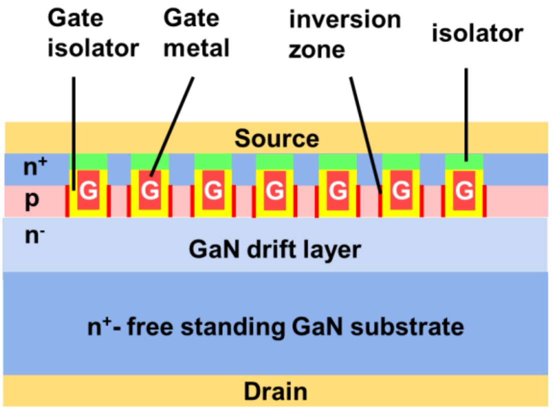

Fig. 1: Schematic cross section of vertical GaN-MISFETs

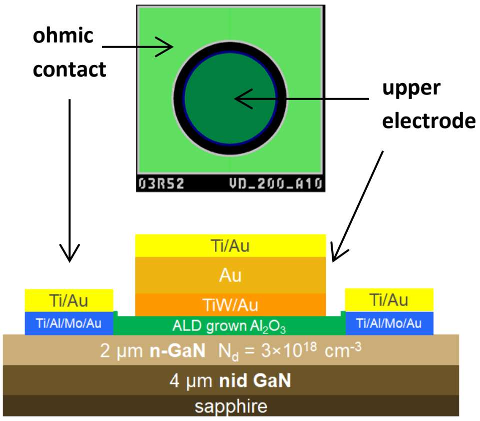

Fig. 2: Schematic of MIS capacitor: top view (top), cross section (bottom)

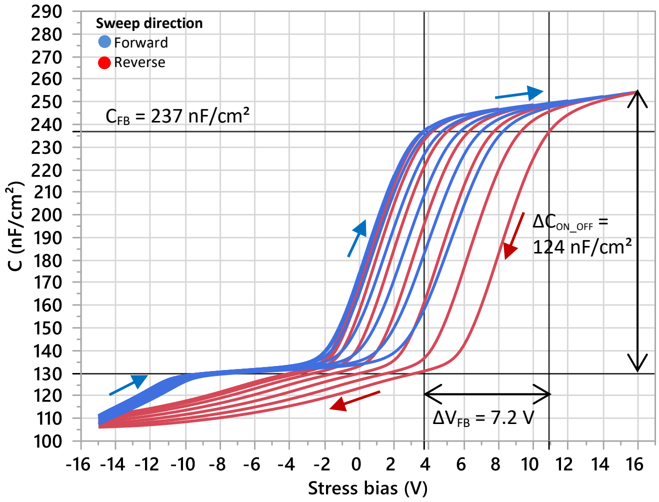

Fig. 3: CV-scan of MIS capacitor with Al_2O_3 deposited by PEALD with NH_3-plasma pre-treatment; forward direction (blue), reverse direction (red)

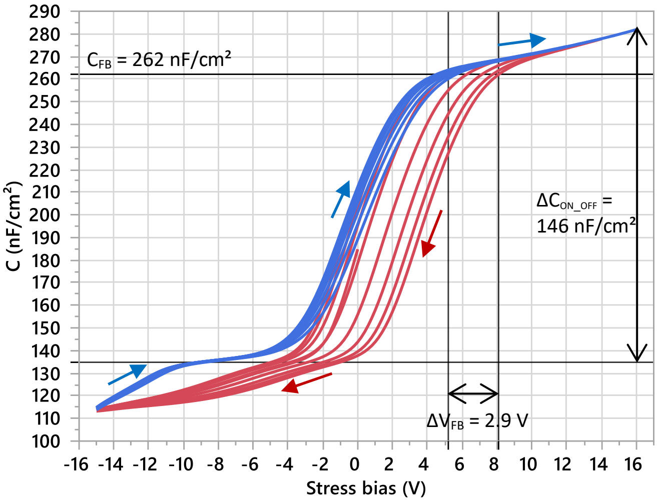

Fig. 4: CV-scan of MIS capacitor with Al_2O_3 deposited by ThALD with NH_3-plasma pre-treatment; forward direction (blue), reverse direction (red)

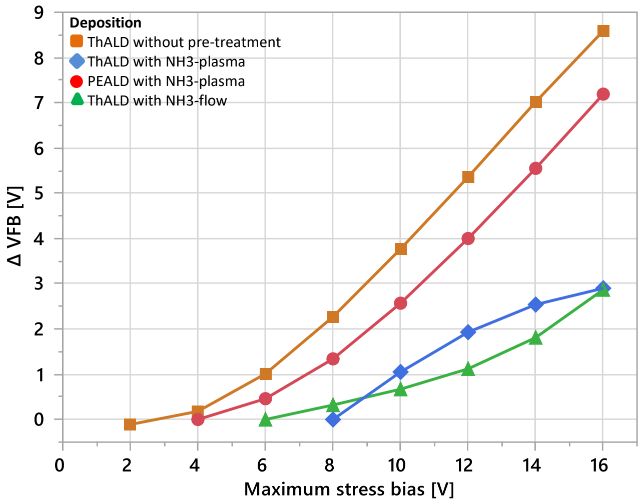

Fig. 5: Flatband voltage shift as a function of the maximum stress bias for different Al_2O_3 films

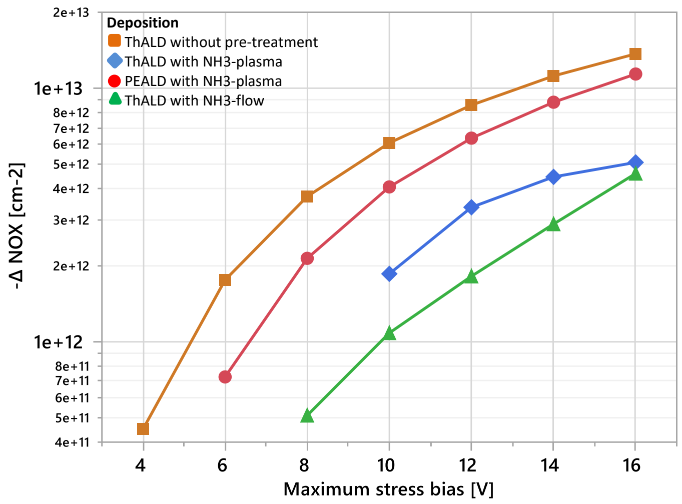

Fig. 6: Stress-induced negative fixed-oxide charges for different Al_2O_3 films